

2SD1511G

Silicon NPN epitaxial planar type darlington

For low-frequency output amplification

■ Features

- Forward current transfer ratio h_{FE} is designed high, which is appropriate to the driver circuit of motors and printer hammer: $h_{FE} = 4000$ to 20000.
- A shunt resistor is omitted from the driver.
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	100	V
Collector-emitter voltage (Base open)	V_{CEO}	80	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	1	A
Peak collector current	I_{CP}	1.5	A
Collector power dissipation *	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

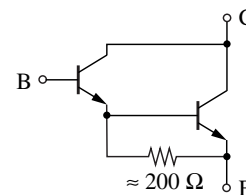
Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

■ Package

- Code
MiniP3-F2
- Pin Name
1: Base
2: Collector
3: Emitter

■ Marking Symbol: P

■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

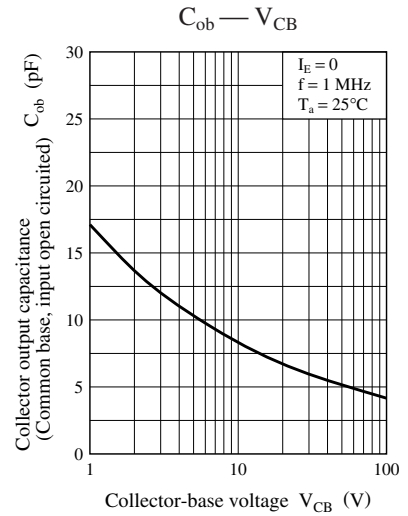
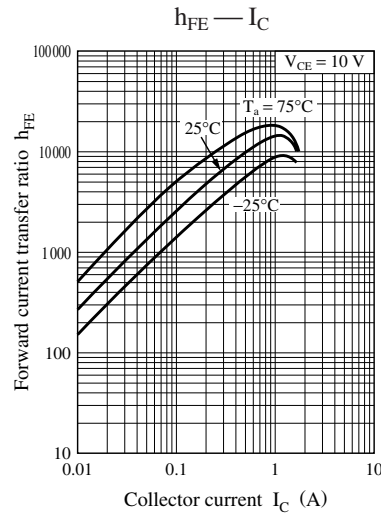
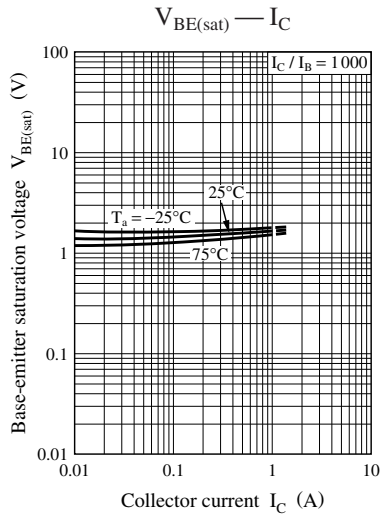
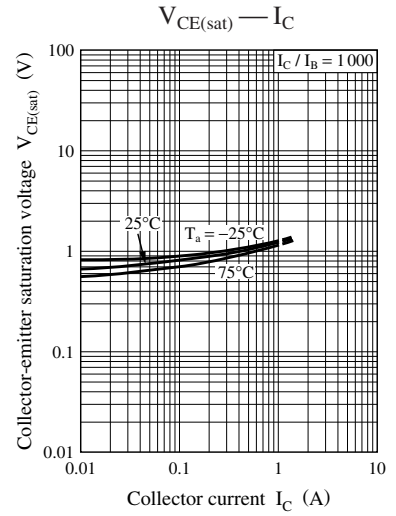
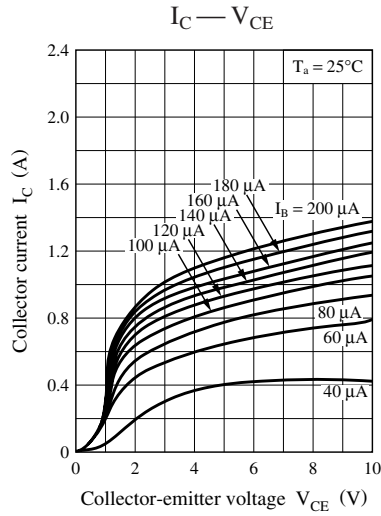
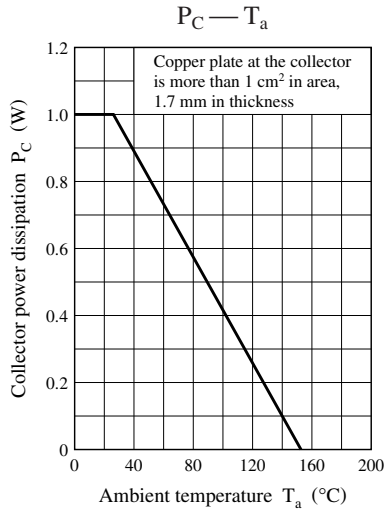
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	100			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	80			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 25 \text{ V}, I_E = 0$			100	nA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 4 \text{ V}, I_C = 0$			100	nA
Forward current transfer ratio *1,2	h_{FE}	$V_{CE} = 10 \text{ V}, I_C = 1 \text{ A}$	4000		40000	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			1.8	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			2.2	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

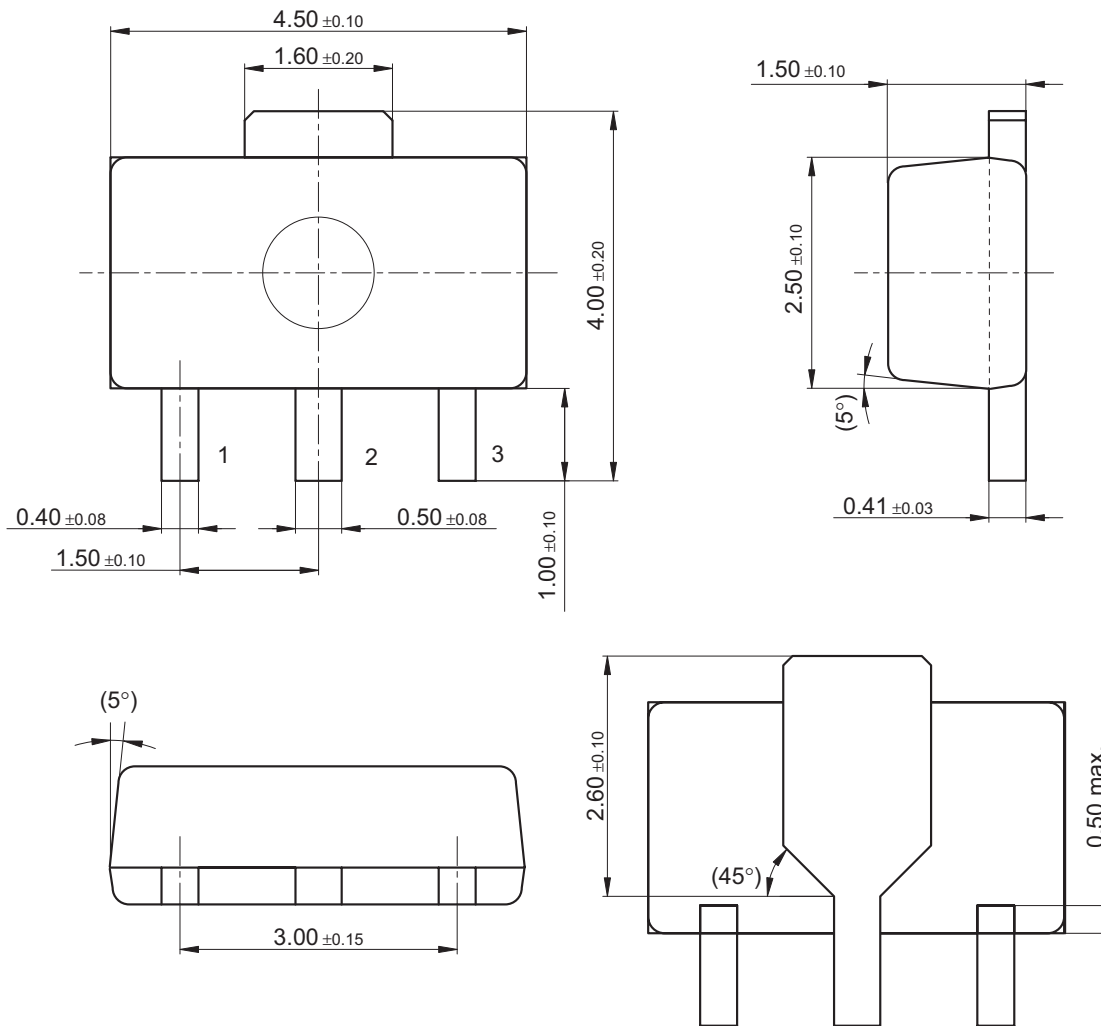
*2: Rank classification

Rank	Q	R	S
h_{FE}	4000 to 10000	8000 to 20000	16000 to 40000



MiniP3-F2

Unit: mm



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